

NCE3018AS

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3018AS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =30V,I_D =18A

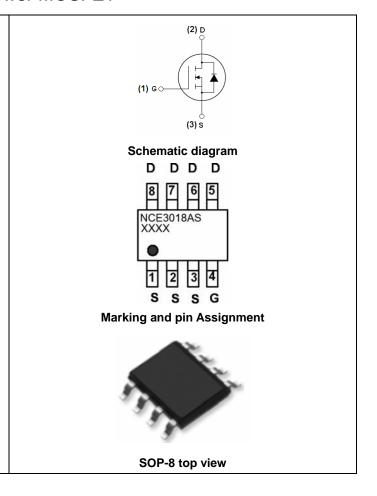
 $R_{DS(ON)}$ < 7m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 10m Ω @ V_{GS} =4.5V

- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3018AS	NCE3018AS	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	18	А
Drain Current-Continuous(T _A =100 °C)	I _D (100℃)	12.7	А
Pulsed Drain Current	I _{DM}	48	А
Maximum Power Dissipation	P _D	3	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	42	°C/W



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Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.9	1.1	1.4	V	
Desire Courses On Otata Desirate and		V _{GS} =10V, I _D =12A	-	5.5	7	- mΩ	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =10A	-	6.5	10		
Forward Transconductance	g FS	V _{DS} =5V,I _D =12A	5	-	-	S	
Dynamic Characteristics (Note4)			-	ı			
Input Capacitance	C _{lss}	\/ -45\/\/ -0\/	-	2100	-	PF	
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, F=1.0MHz	-	460	-	PF	
Reverse Transfer Capacitance	C _{rss}	r=1.0lvln2	-	230	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	20	-	nS	
Turn-on Rise Time	t _r	V_{DD} =10 V , I_D =12 A	-	15	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{GEN} =2.7 Ω	-	60	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg	\/ -15\/ -12\	-	41	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =15V, I_D =12A, V_{GS} =10V	-	14	-	nC	
Gate-Drain Charge	Q_{gd}	v GS-10 v	-	11	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	18	Α	

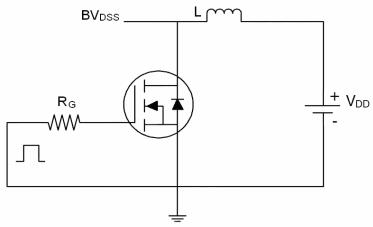
Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

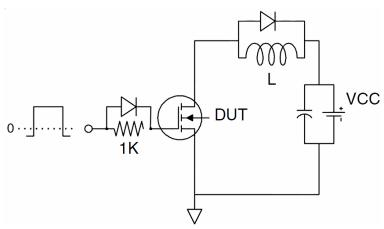
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Test Circuit

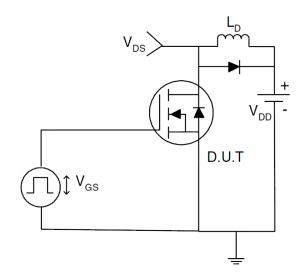
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Pb Free Product



Typical Electrical and Thermal Characteristics (Curves)

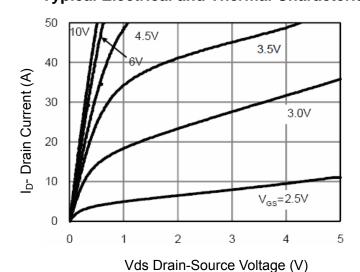


Figure 1 Output Characteristics

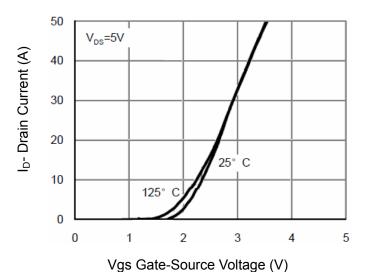


Figure 2 Transfer Characteristics

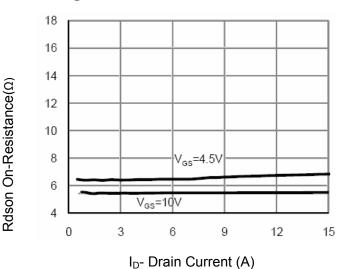


Figure 3 Rdson- Drain Current

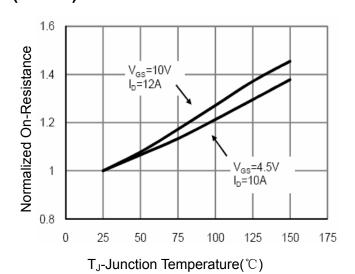


Figure 4 Rdson-Junction Temperature

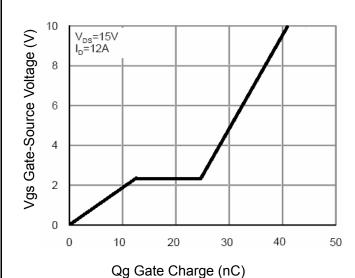


Figure 5 Gate Charge

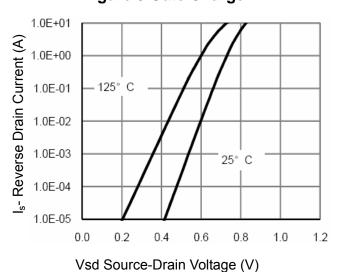


Figure 6 Source- Drain Diode Forward



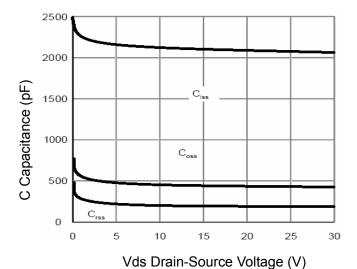
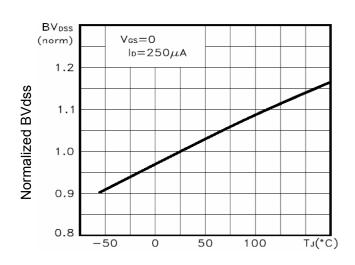
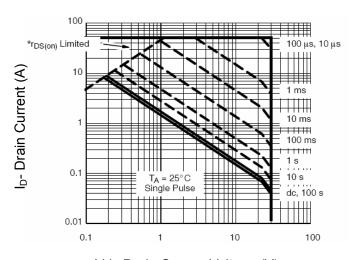


Figure 7 Capacitance vs Vds

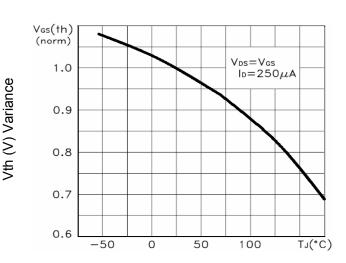


T_J-Junction Temperature(°C)

Figure 9 BV_{DSS} vs Junction Temperature

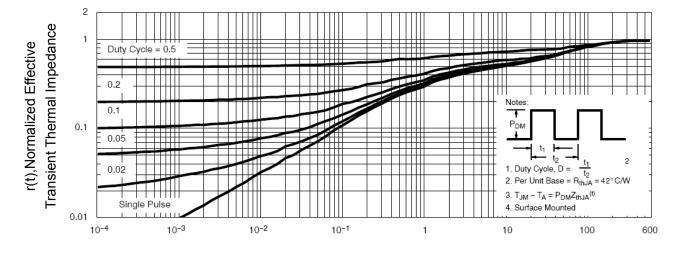


Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



 $\mathsf{T}_{\mathsf{J}} ext{-Junction Temperature}({}^{\mathbb{C}})$

Figure 10 V_{GS(th)} vs Junction Temperature



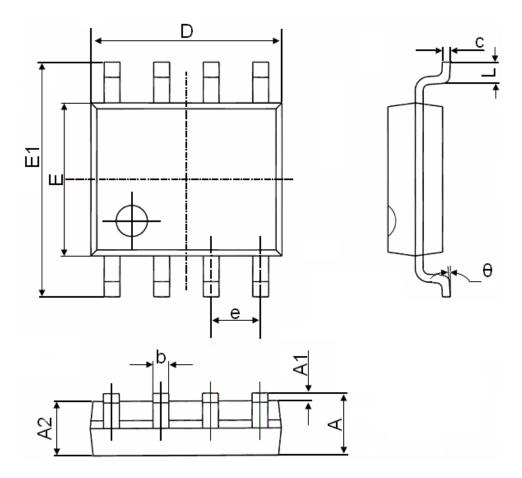
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

Pb Free Product



SOP-8 Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	1.270(BSC)		(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



http://www.ncepower.com

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